

Title (en)

DUAL-SOURCE, SINGLE-CHAMBER METHOD AND APPARATUS FOR SPUTTER DEPOSITION

Title (de)

SPUTTERABSCHIEDUNGSVERFAHREN UND VORRICHTUNG MIT ZWEI QUELLEN UND EINER KAMMER

Title (fr)

PROCEDE A DEUX SOURCES ET A CHAMBRE UNIQUE ET APPAREIL DE PULVERISATION

Publication

EP 1438442 A1 20040721 (EN)

Application

EP 02776033 A 20020927

Priority

- US 0230867 W 20020927
- US 32533201 P 20010927

Abstract (en)

[origin: WO03027352A1] The present invention relates to a dual-source, single-chamber method and apparatus for epitaxial sputter deposition of epilayers and high quality films. The apparatus for performing the method includes a first sputtering source (2) for the sputtering of an epitaxial film on a substrate (6). A second sputtering source 4 is for the sputtering of reactive materials to create a getter on a cryogenic shroud (8). The first sputtering source (4) and the substrate (6) are surrounded by the cryogenic shroud (8).

IPC 1-7

C23C 14/34

IPC 8 full level

C23C 14/34 (2006.01); **C23C 14/56** (2006.01); **C30B 23/02** (2006.01); **H01J 37/34** (2006.01)

CPC (source: EP KR)

C23C 14/34 (2013.01 - KR); **C23C 14/564** (2013.01 - EP); **C30B 23/02** (2013.01 - EP); **H01J 37/32834** (2013.01 - EP); **H01J 37/34** (2013.01 - EP)

Citation (search report)

See references of WO 03027352A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)

WO 03027352 A1 20030403; CN 1561405 A 20050105; EP 1438442 A1 20040721; JP 2005504172 A 20050210; KR 20040044994 A 20040531

DOCDB simple family (application)

US 0230867 W 20020927; CN 02819133 A 20020927; EP 02776033 A 20020927; JP 2003530912 A 20020927; KR 20047004398 A 20020927